

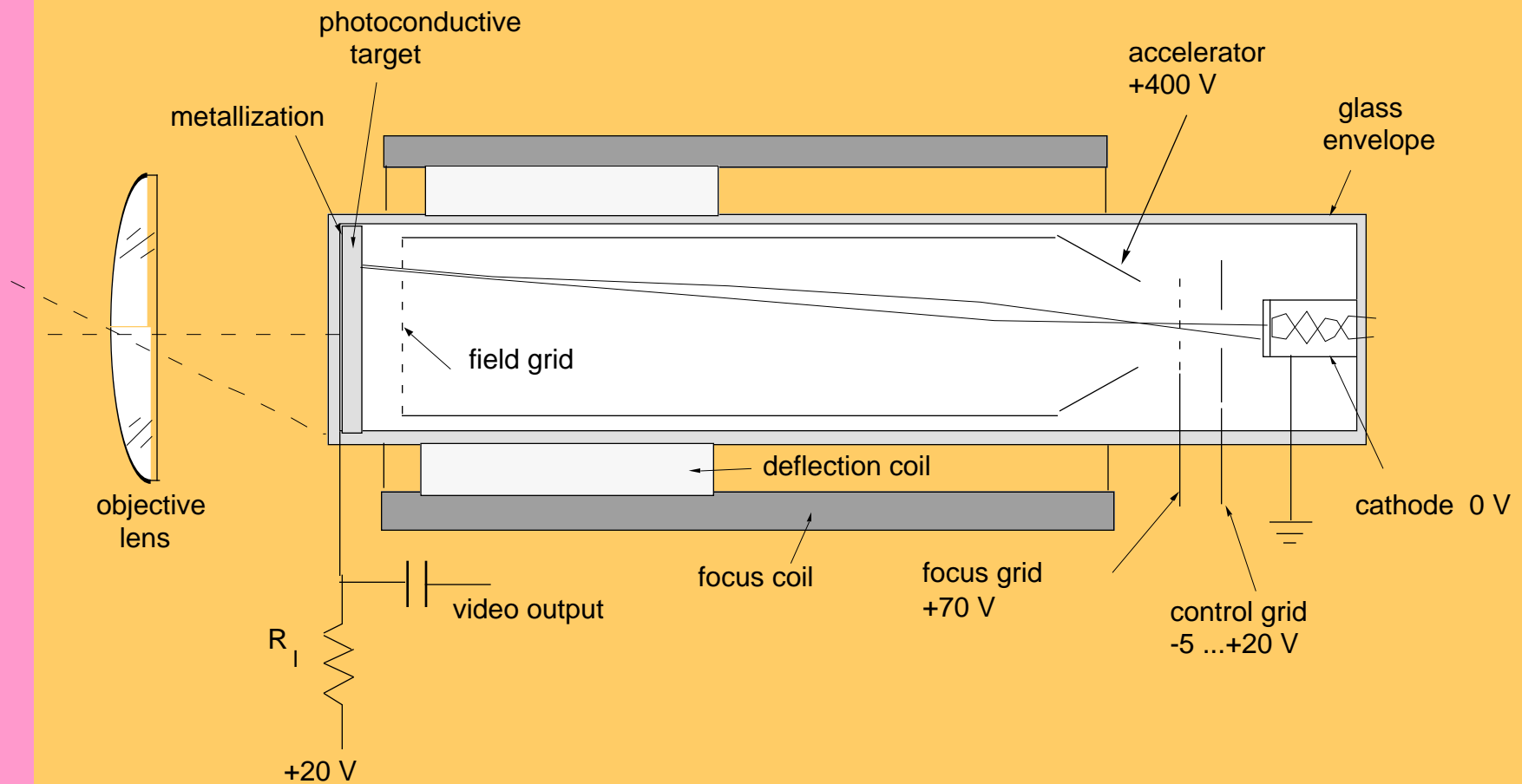
Categorization of Image Devices

- Image Pickup detectors: individual pixel are organized serially in a single electrical signal, suitable for transmission (TV, etc.) or processing
- Direct-Vision detectors: an intensified or spectrally converted replica of the input image is supplied at an output screen

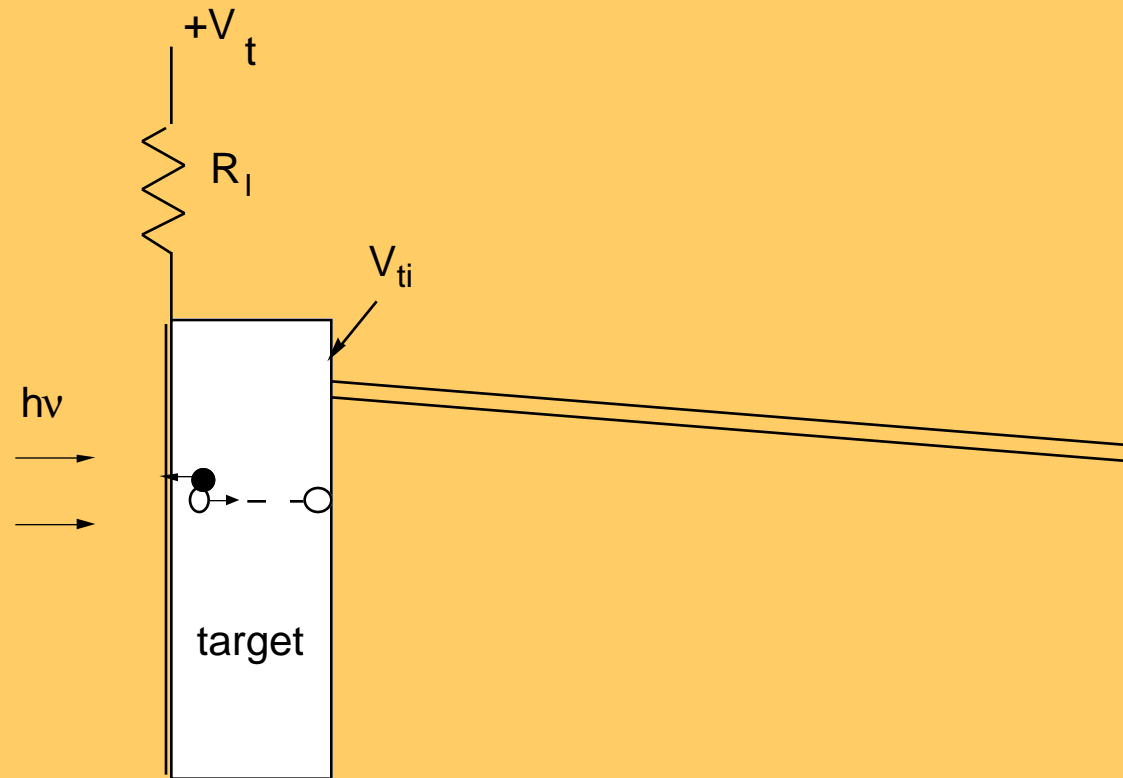
Requisites for Image Pickup devices:

- ◇ a **photosensitive surface** to accommodate $N \times M$ pixels
- ◇ a provision to **single out** the individual image pixels
- ◇ an arrangement for **sequential readout** of photogenerated charge
- ◇ an **integration of the photogenerated charge** between successive readouts, i.e., the frame period T_f .

The vidicon

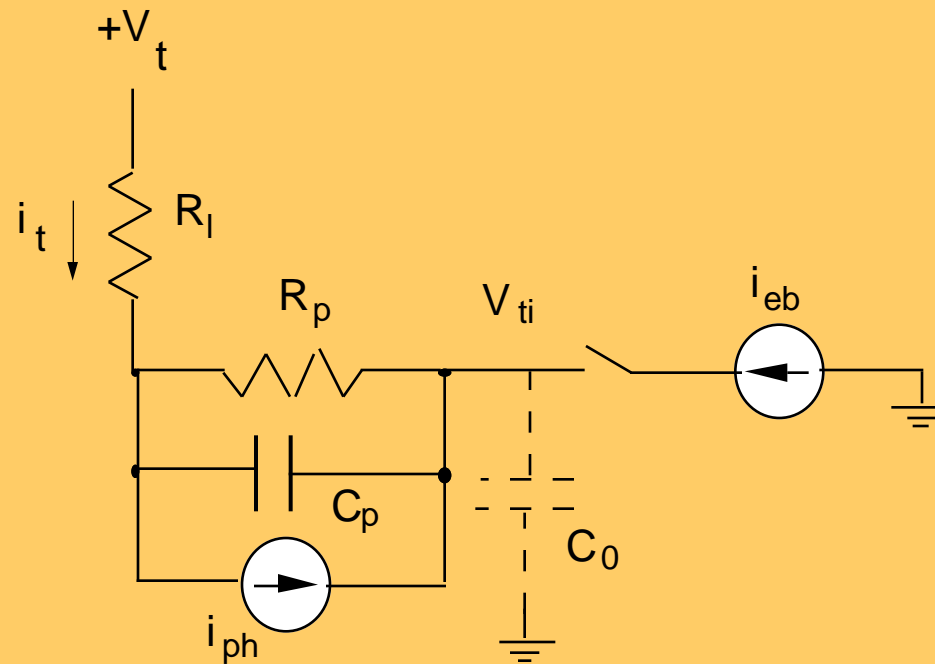


Target storage



$$V_{ti} = Q/C_t = \sigma p T_f / C_t$$

Target readout



$$i_t = Q/t_p = \sigma p T_f / t_p$$

$$f_2 = 1/2\pi(R_l // R_p)(C_p + C_0)$$

Internal gain and beam effects

- Actually, the target is a PC and yields a photoconductive *gain* M . Thus, spectral sensitivity is $M\sigma$.
- Trapping time τ_n (determining gain $M=\tau_n/T$) is kept less than or comparable to frame period T_f (16 or 20 ms), to avoid *image lag*.
- Gain is proportional to *target voltage* V_t - an easy way to adjust the video current.
- Electron beam current i_{pe} shall be $> i_t$ (of brightest pixel), or charge deposited by beam $Q_{pe}=i_{pe}t_p$ will not compensate $Q=\sigma p T_f (=i_t t_p)$, leaving a residual $Q-Q_p$ after a frame. Next frame residual charge doubles, and so on until charge spreads transversally on adjacent pixels, the *blooming* effect.
- Best with i_{pe} as small as possible, to: (i) make crossover small; (ii) keep the beam-readout noise low.

Signal and noise

The average level of the video current i_t is calculated as:

$$i_t = \sigma P_q = \sigma A E_t = \sigma A \delta E_{sc} / 4(F/)^2$$

where E_t is the target illuminance, given by $\delta E_{sc} / 4(F/)^2$ using scene illumination, δ =scene diffusivity and $F/$ = objective lens F-number.

Noise current variance as:

$$\sigma_{it}^2 = 2e [1+2(M-1)^2](i_t+I_0)B + 2e\kappa i_{pe}B + 4kTB/R_l$$

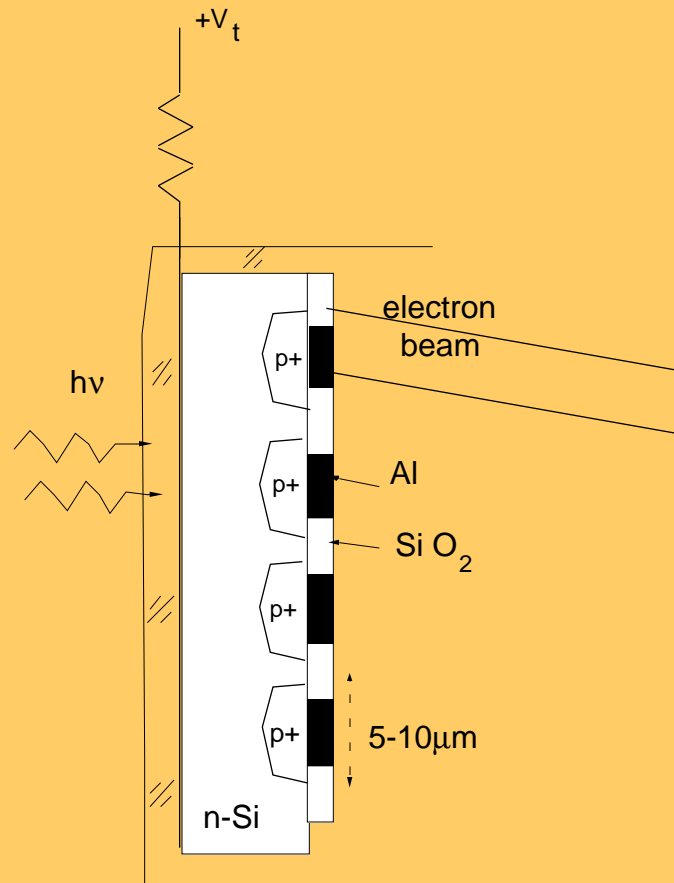
where i_t and I_0 are the signal and target dark-current, second term is the electron beam readout noise (with κ a factor about unity), and the last term is the load Johnson noise.

A sample of vidicons

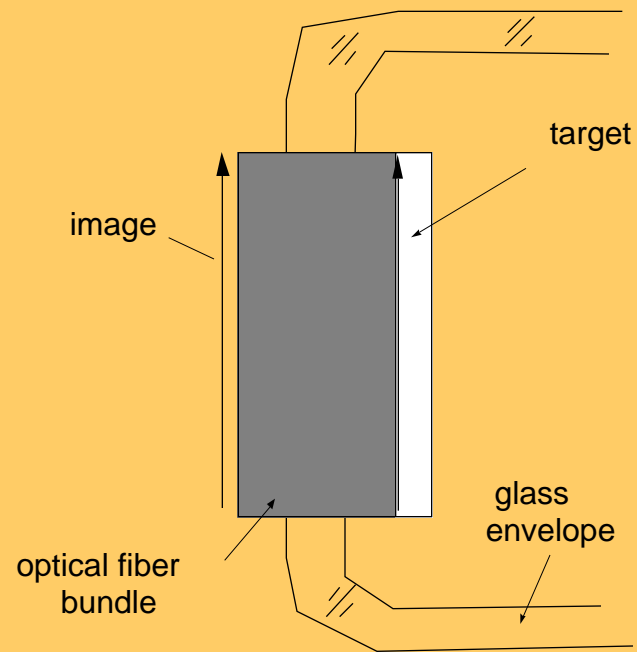


from: 'Photodetectors', by S. Donati, Prentice Hall 2000

Si-target vidicon



Fiberoptics faceplate vidicon



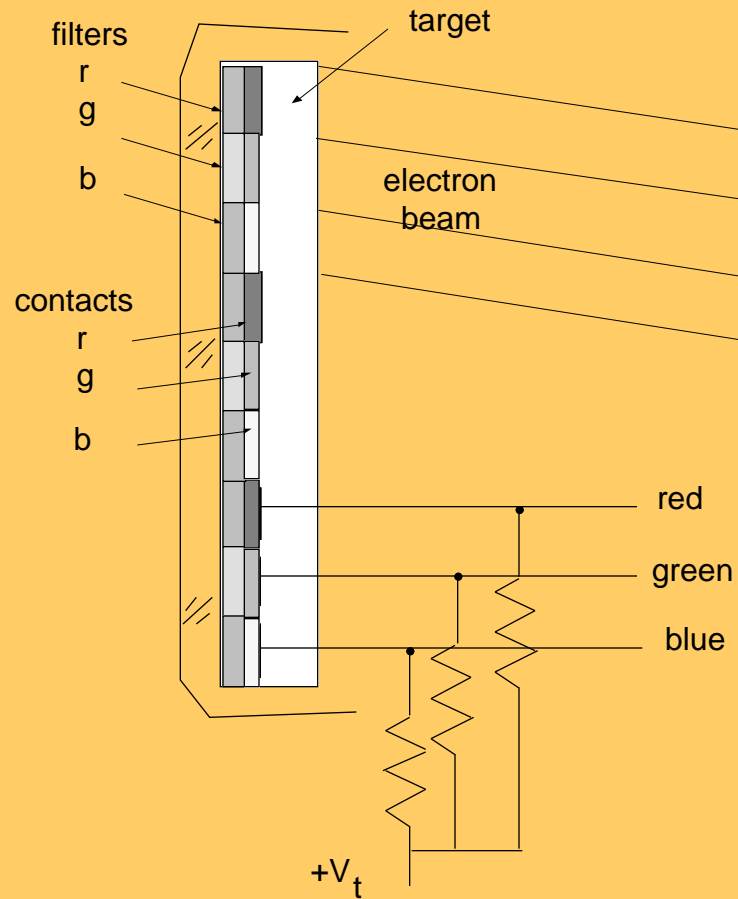
Fiberoptics and Intensified Vidicon

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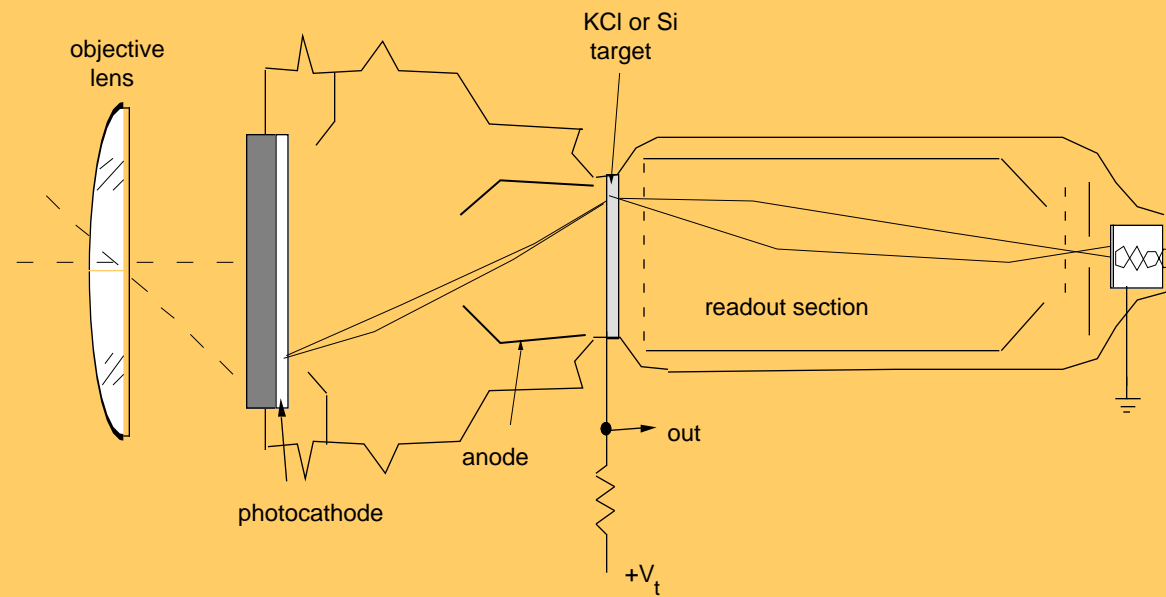


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Color vidicon



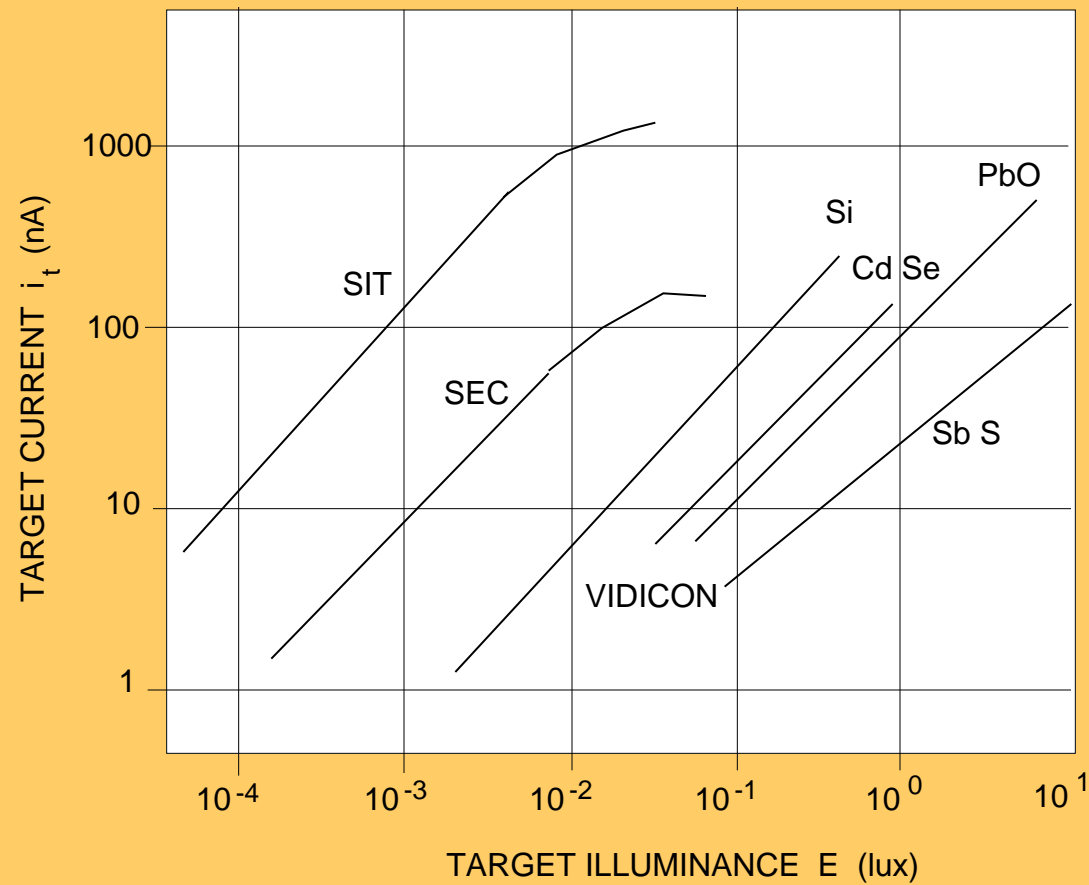
Intensified vidicon



Vidicon parameters

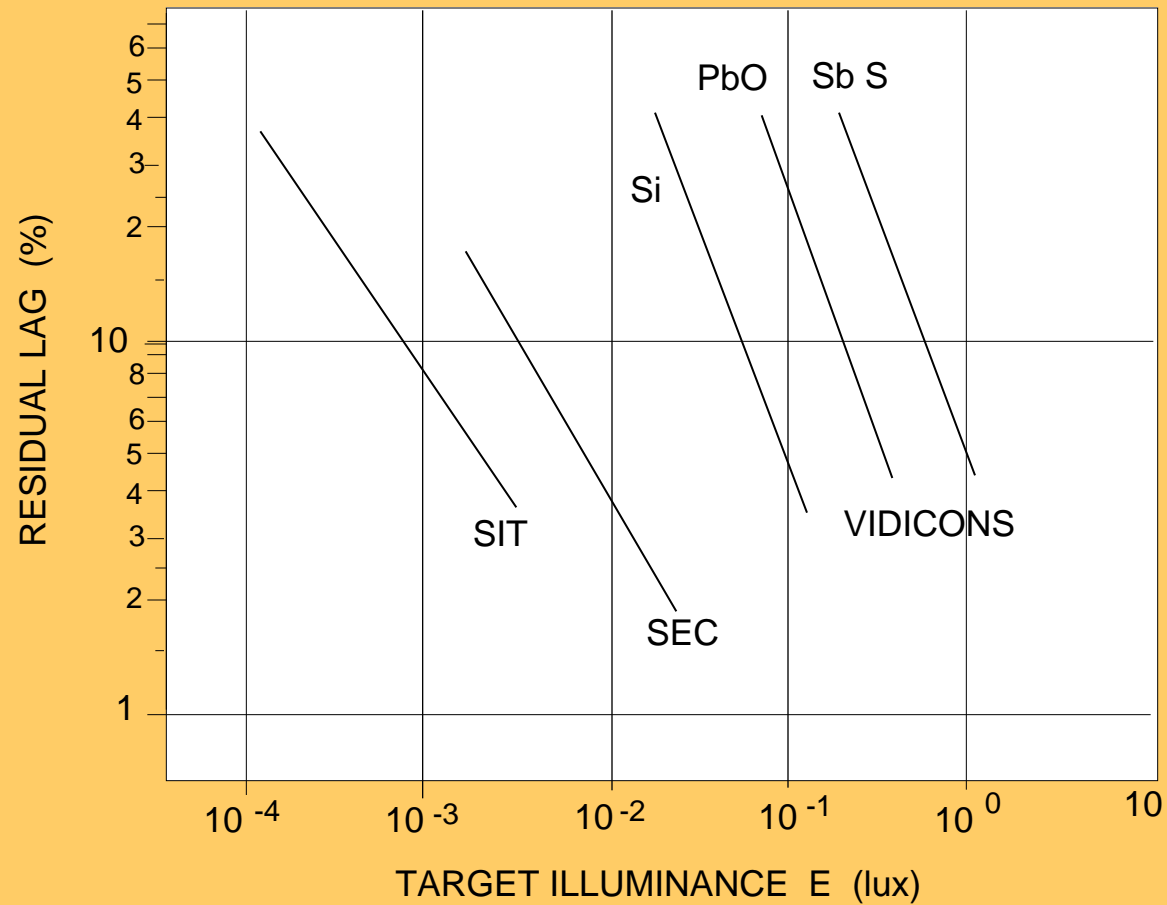
- *luminous or spectral sensitivity*, given $\mu\text{A}/\text{lm}$ or $\mu\text{A}/\text{W}$
- *dark current* I_0 , in the range 1-10 nA typ. for a vidicon;
- *video dynamic range*, ratio of the max. to min. useful signal, limited by saturation and noise, usually 2-3 decades;
- *linearity* of response, or γ (gamma) of the $\log i_t$ vs $\log E_t$ curve, given by the slope of the curves;
- *image format*, or the *diagonal* (expressed in inches) of the image scan area, which influences the total number of pixels;
- *spatial resolution*, expressed in lp/mm or lp/fr (line-pairs per mm or per frame) that can be resolved;
- *residue or lag*, usually specified as the percentage of signal persisting after three frames;
- *uniformity* υ of the target response from point to point.
- *image defectiveness*, in the form of white/black fixed points appearing on the image, called *blemishes*.

‘Gamma’ curve of image pickup tubes



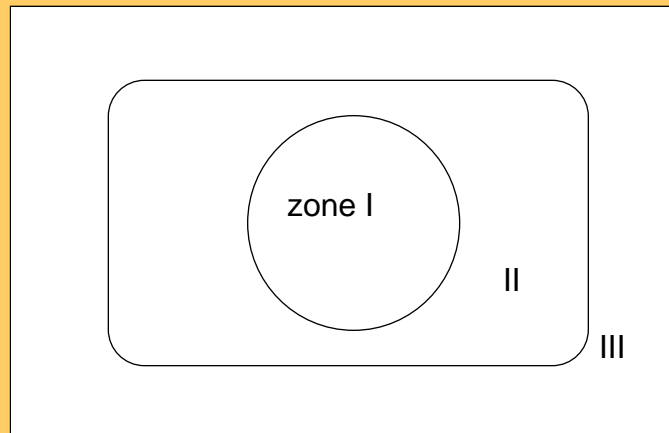
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Lag in image pickup tubes



from: 'Photodetectors', by S. Donati, Prentice Hall 2000

Blemish classification

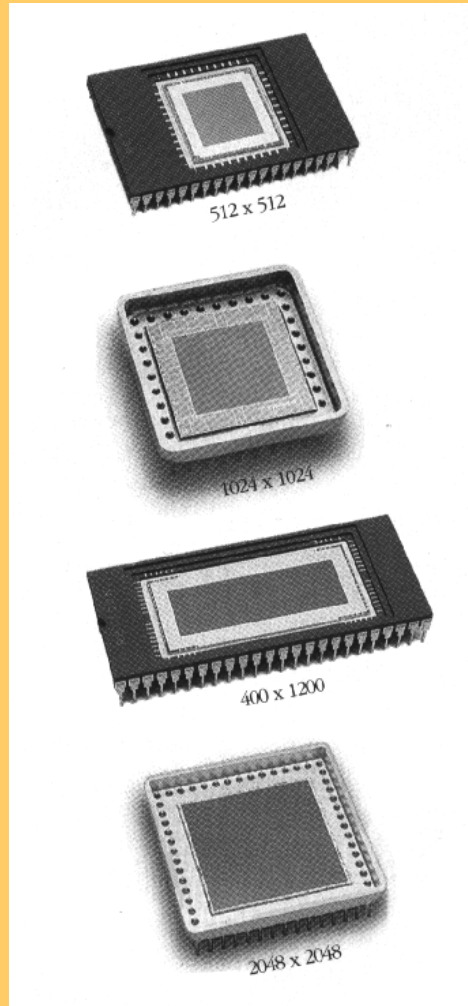


In zones I, II, II, a top quality (A-class) tube may have 0, 1, 3 defects not larger than 1 pixel, a class B 1, 3, 10 and a industrial-class (X-class) 5, 20, >20.

Tube price is dependent on this specification, with a typical ratio 10: 5 :1 (at equal size).

CCDs

Popular
silicon CCDs
in several
formats



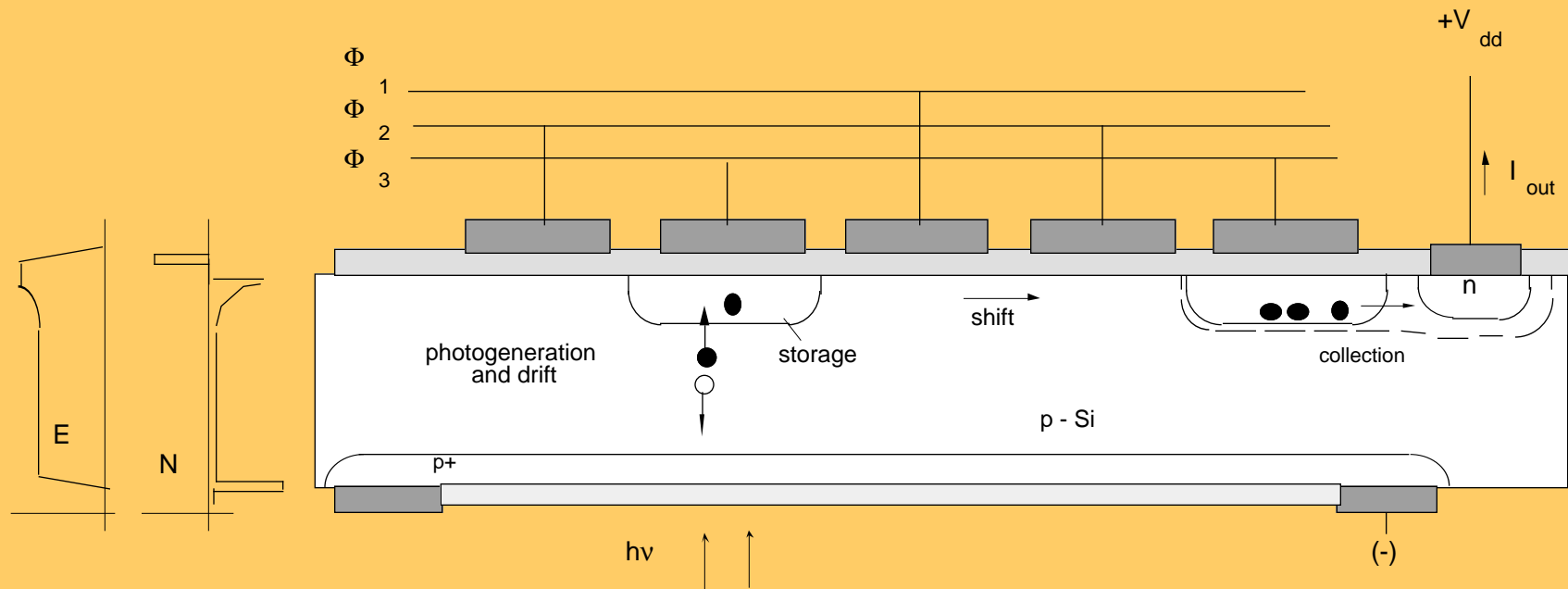
512x512 pixels

1024x1024

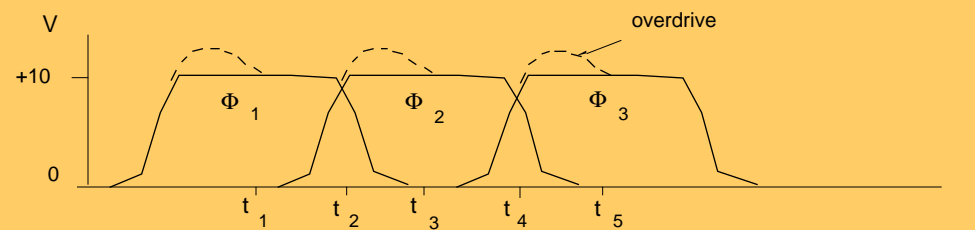
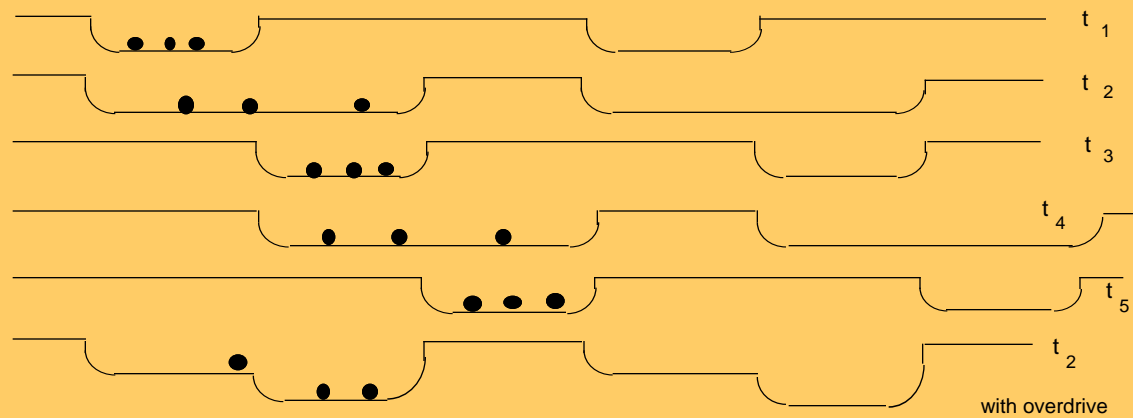
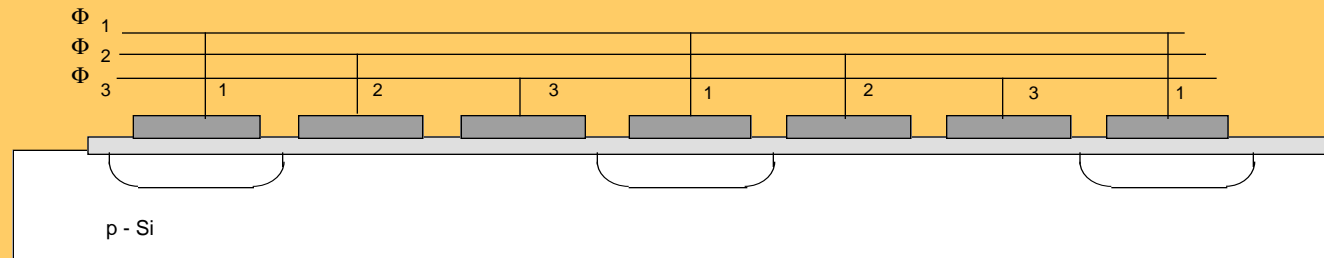
400x1200

2048x2048

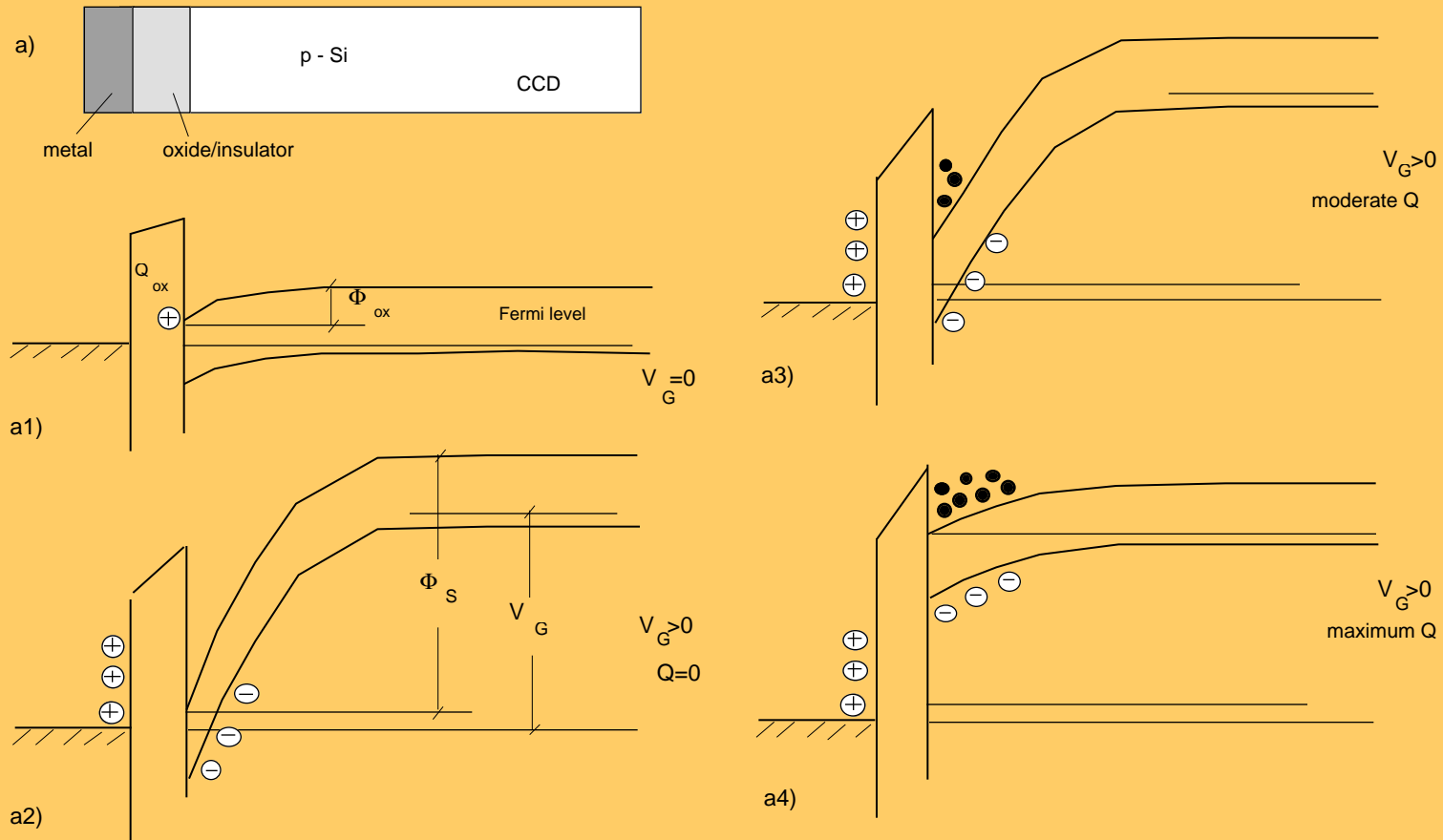
CCD basic structure



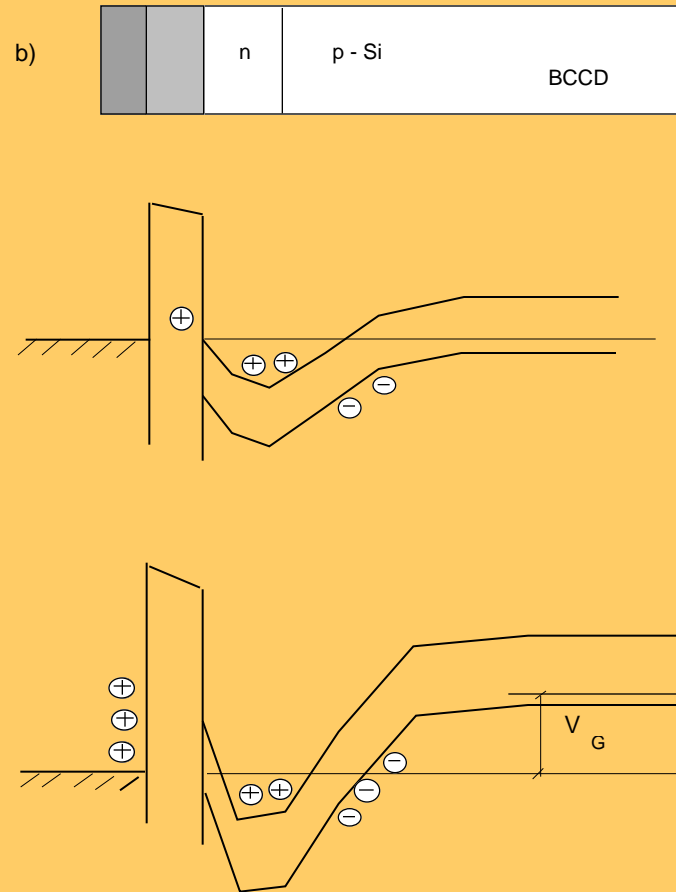
Charge transfer mechanism



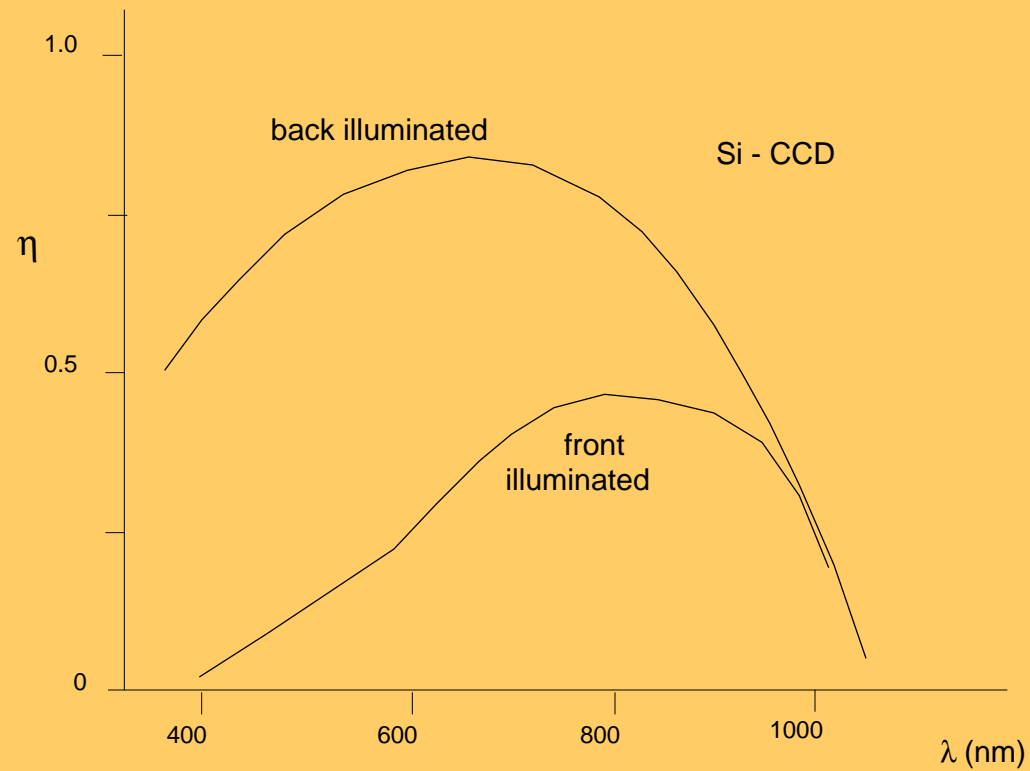
Potential well



Buried channel



Optical entrance



A few results about electrical parameters

- Potential well: $\Phi_s = V_G - (\Phi_{ms} - \Phi_{ox}) - e(WN_A + N)/C_{ox}$
well depth: $W = [2\epsilon_s \Phi_s / eN_A]^{1/2}$
depletion capacitance: $C_s = \epsilon_s / W = [e\epsilon_s N_A / 2\Phi_s]^{1/2} (\ll C_{ox})$
- Saturation charge:
strong inversion condition: $\Phi_s = 2\Phi_F = (2kT/e) \ln(N_A/n_i)$
saturation charge density: $Q_{max} = C_{ox} V_G = \epsilon_{ox} V_G / w_{ox}$
- Dark current:
$$I_d = I_{g-r} + I_d + I_{ss} = Ae n_i W / 2\tau + Ae n_i^2 D_n / L_n N_A + Ae n_{ss} / 2\tau$$

CCD frequency response

sources of *intrinsic* response frequency-cutoff:

- photodetection (drift/diffusion time),
- image sampling in pixels (integration and dump),
- scanning and readout of the charge packets (transfer).

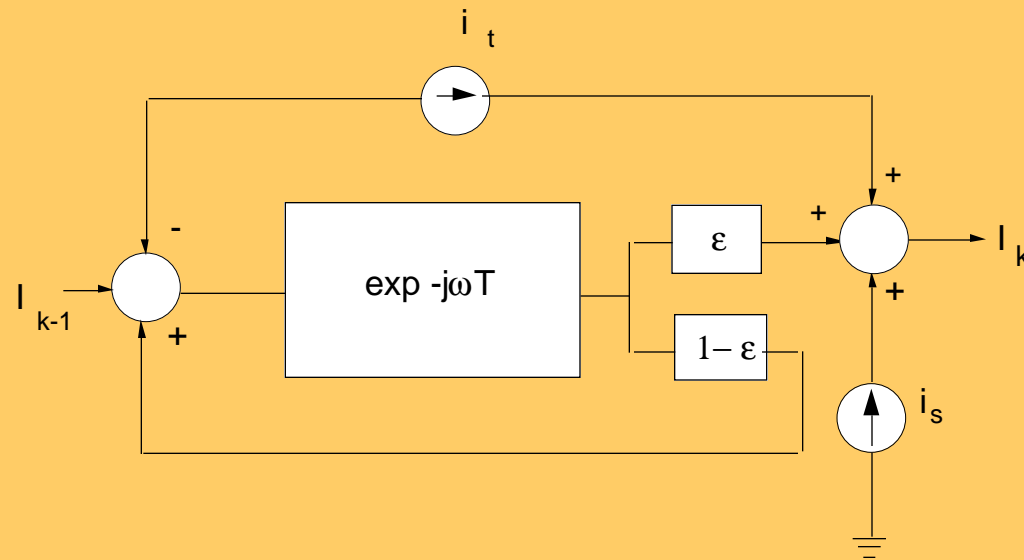
sources of *extrinsic* response frequency-cutoff:

- preamplifier or output front-end (readout section).

For each of the above, a transfer function $F(\omega)$ will be computed, and the product of cascaded $F(\omega)$ will give the overall cutoff - to be not smaller than the video signal frequency f_v .

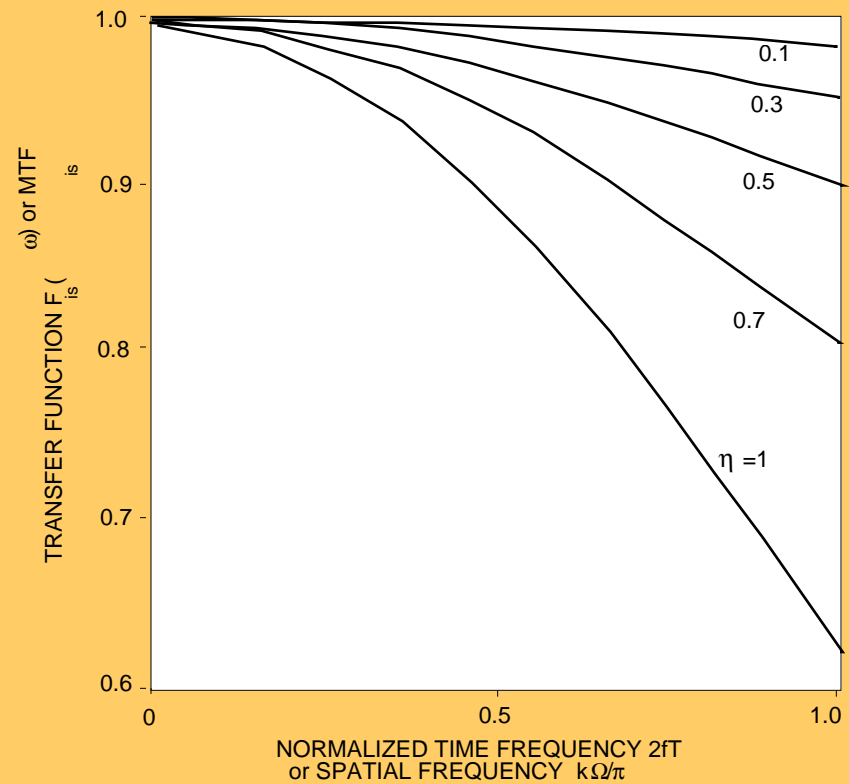
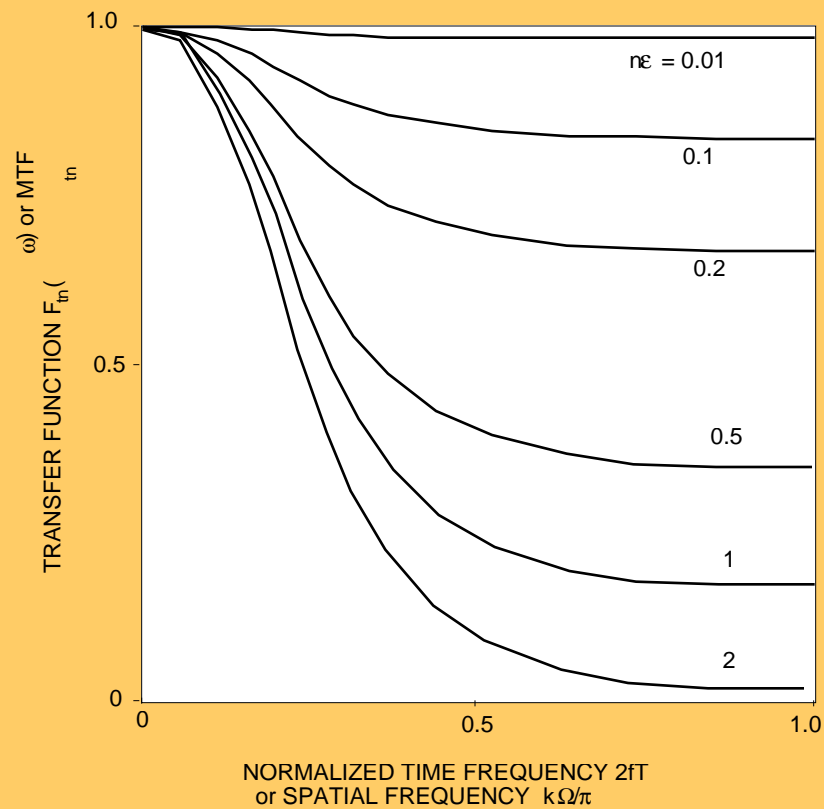
Important to note, $F(\omega)$ is connected to the spatial resolution function $F(k)$ of the device: scanning in time t_p pixels spaced by W , the scanning speed is $v=W/t_p$ and angular (time) frequency ω (rad/s) is related to angular (spatial) frequency k (rad/mm) of the image: $v=\omega/k$.

Cell equivalent circuit

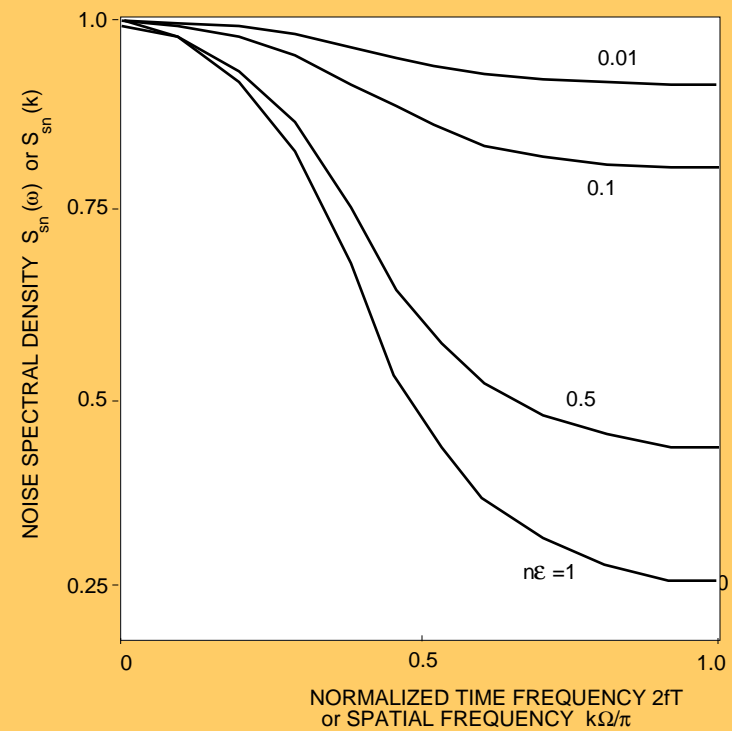
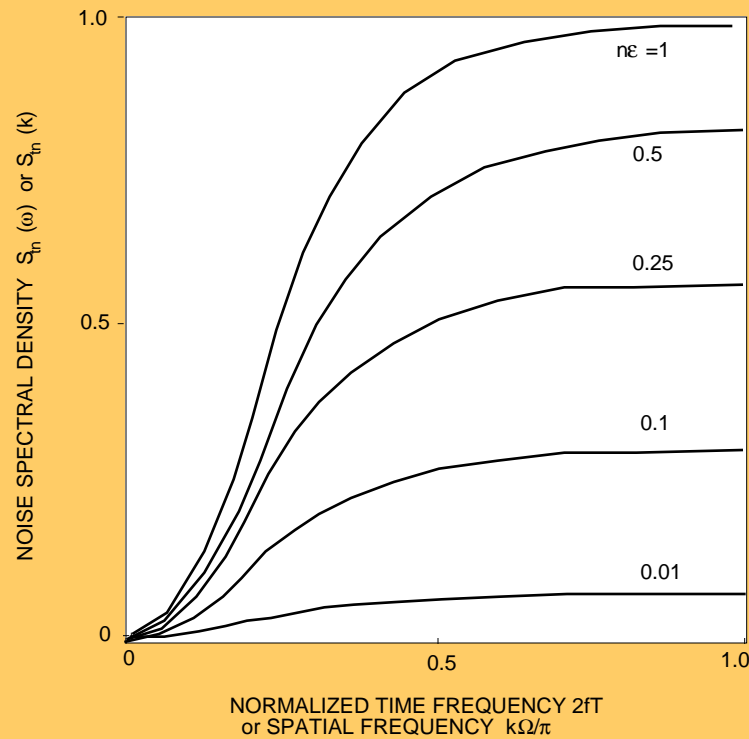


k -th cell is schematized by a delay T (clock phase) , a transfer inefficiency ϵ and shot-noise generators i_t (transfer) and i_s (storage)

CCD transfer frequency-response



Spectral density of transfer and storage noise



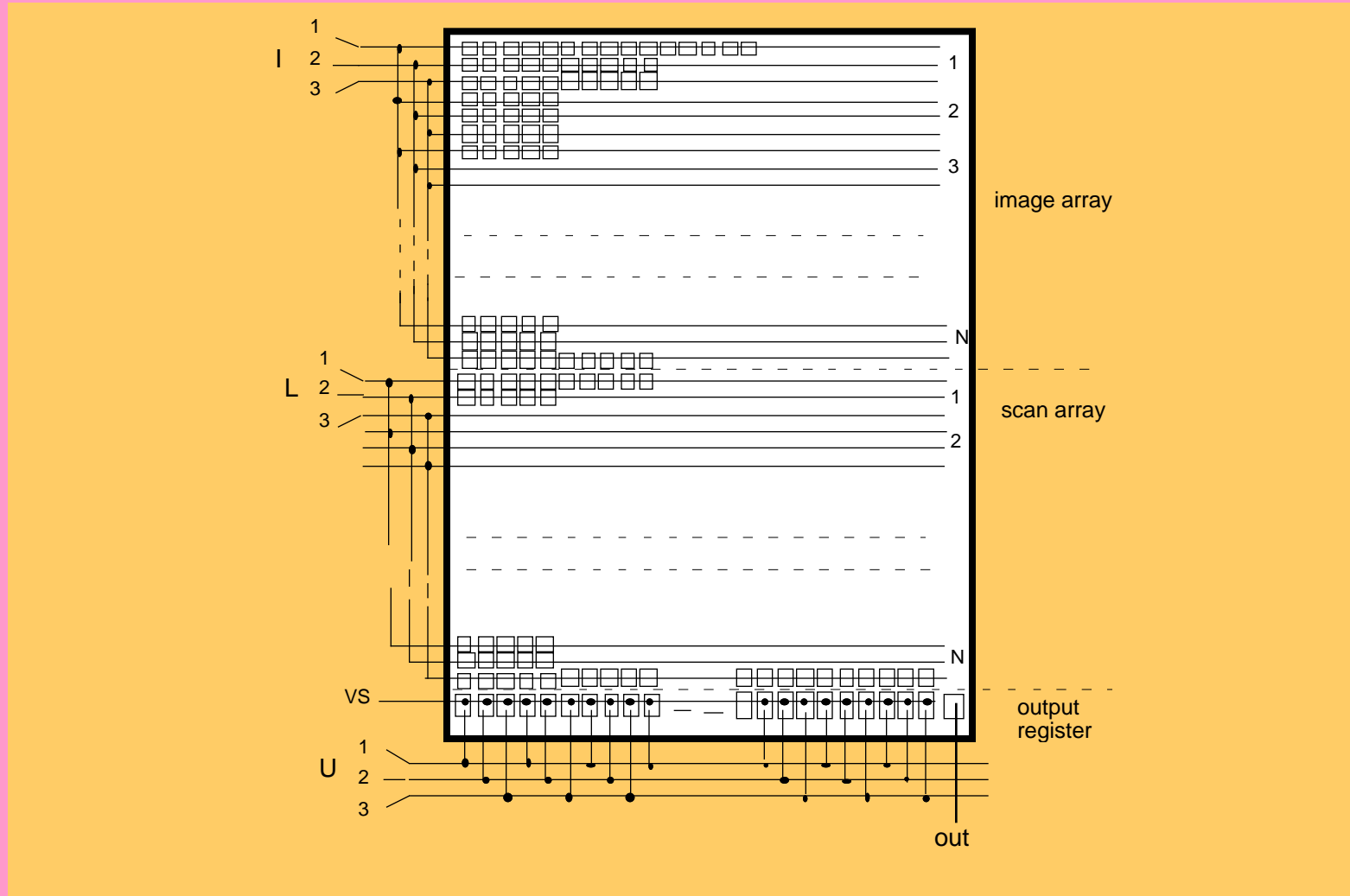
Resumé on intrinsic cutoff and noise

Summarizing the above result:

- frequency cutoff: *transfer* has a severe effect, requiring $n\epsilon < 0.2$ to avoid loss respect to Nyquist frequency $1/2T$
sampling gives a minor loss near $1/2T$ even with complete cell filling ($\eta=1$)
- noise: *transfer* has a minor effect (zero in dc), about $2nq_{ph}/T$ at $n\epsilon=0.2$
storage is max in dc, then damps off; at $n\epsilon=0.2$ gives $(0.7-1) 2nq_s/T$

In practice, storage noise dominates in surface-channel CCDs, while in buried-channel CCDs it is strongly reduced and one can achieve a performance limited by the dark current noise.

Image organization: frame-transfer CCD



Detail of double-level contacts

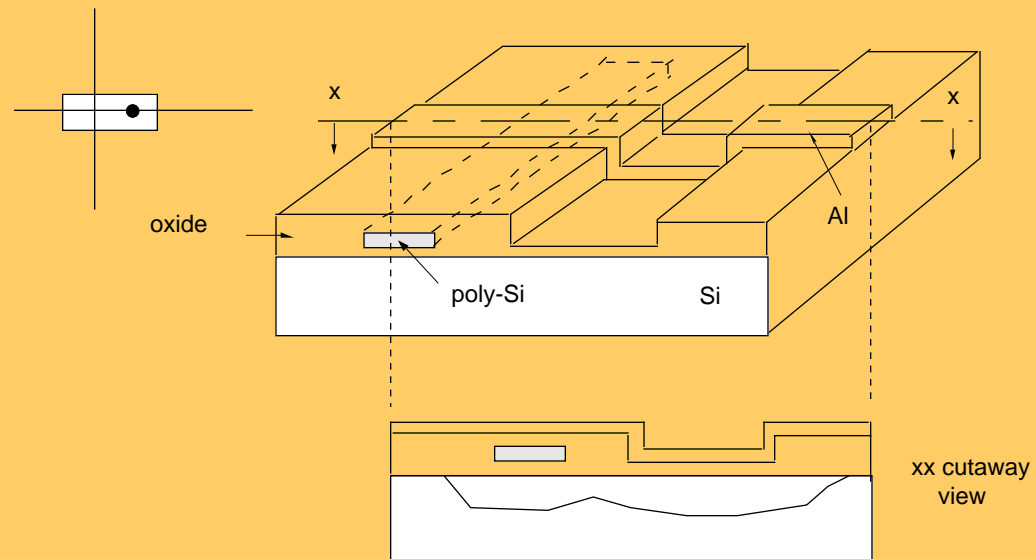


Image organization: interline-transfer CCD

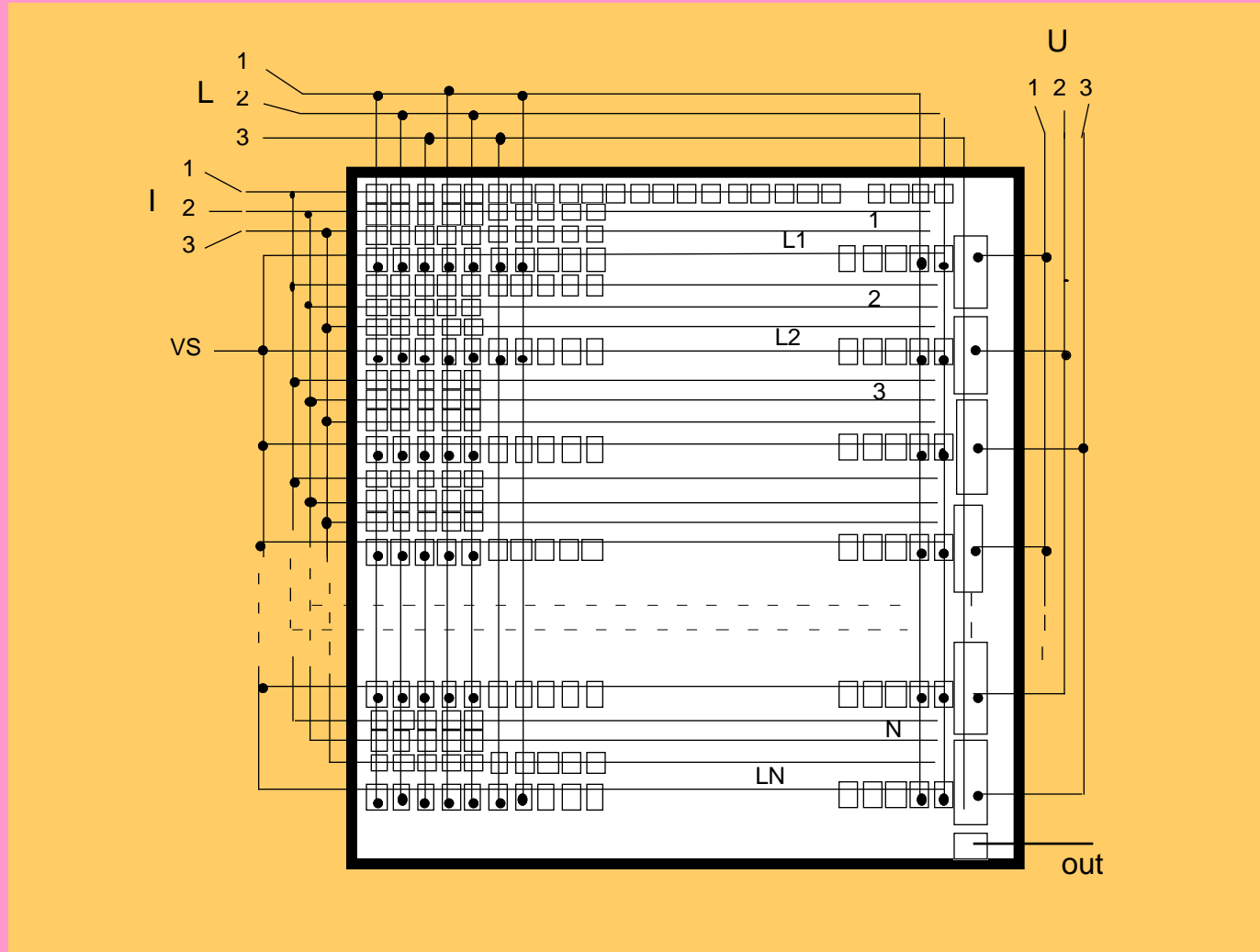
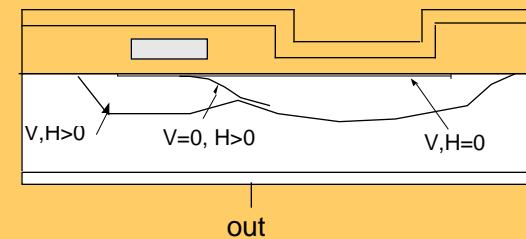
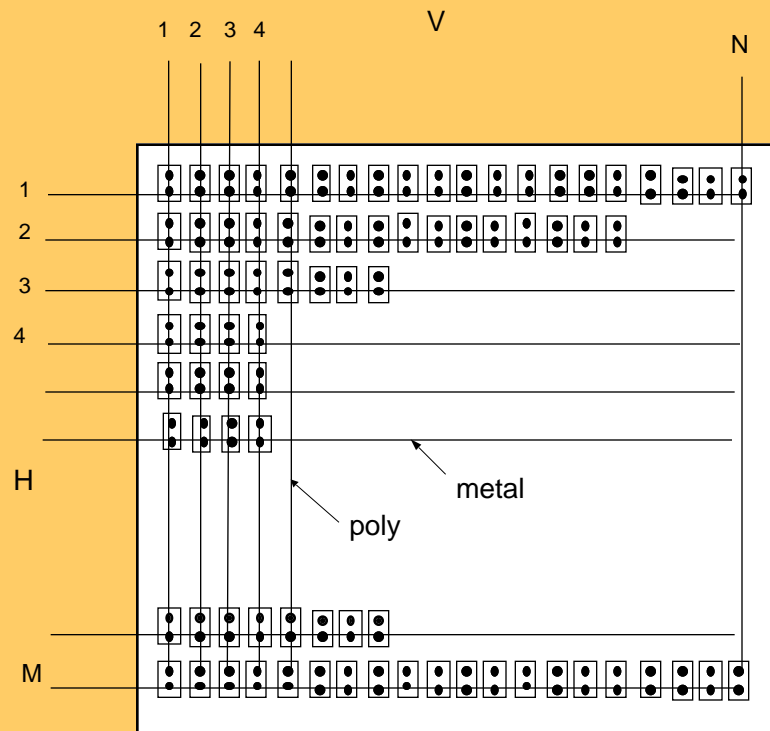
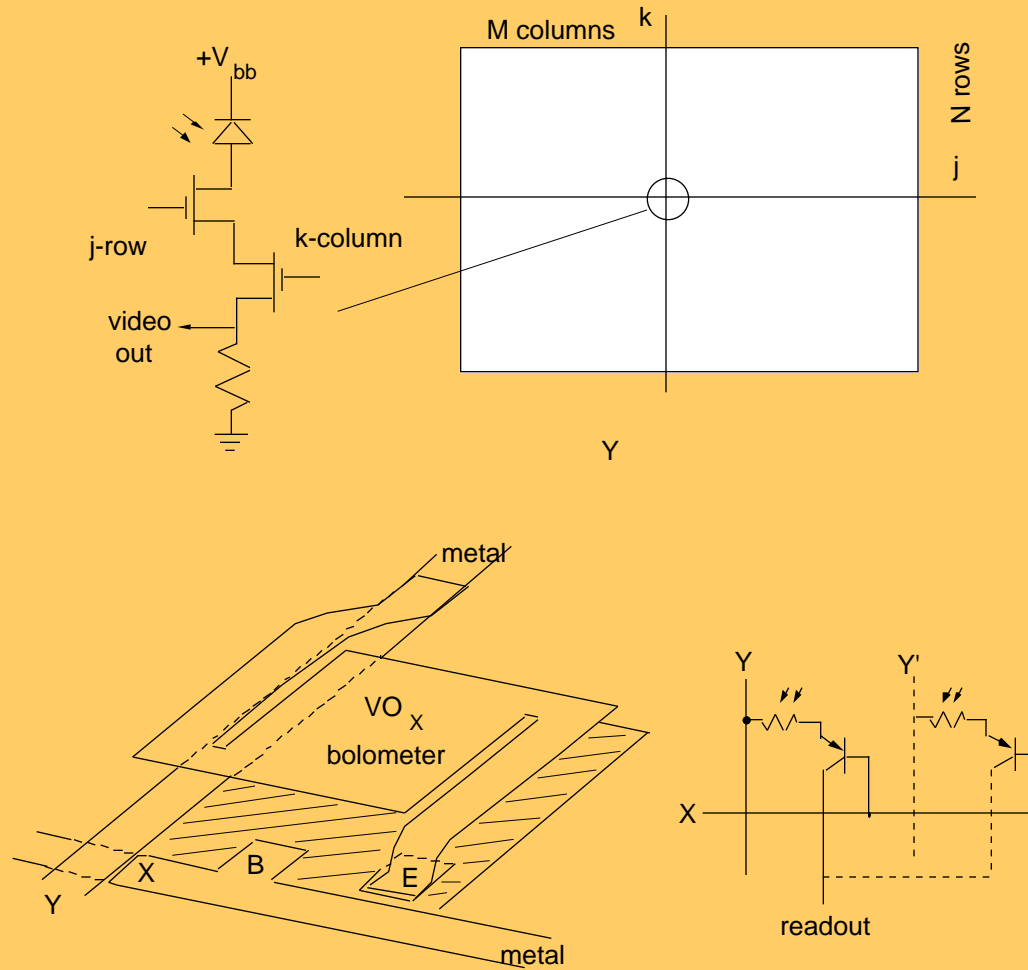


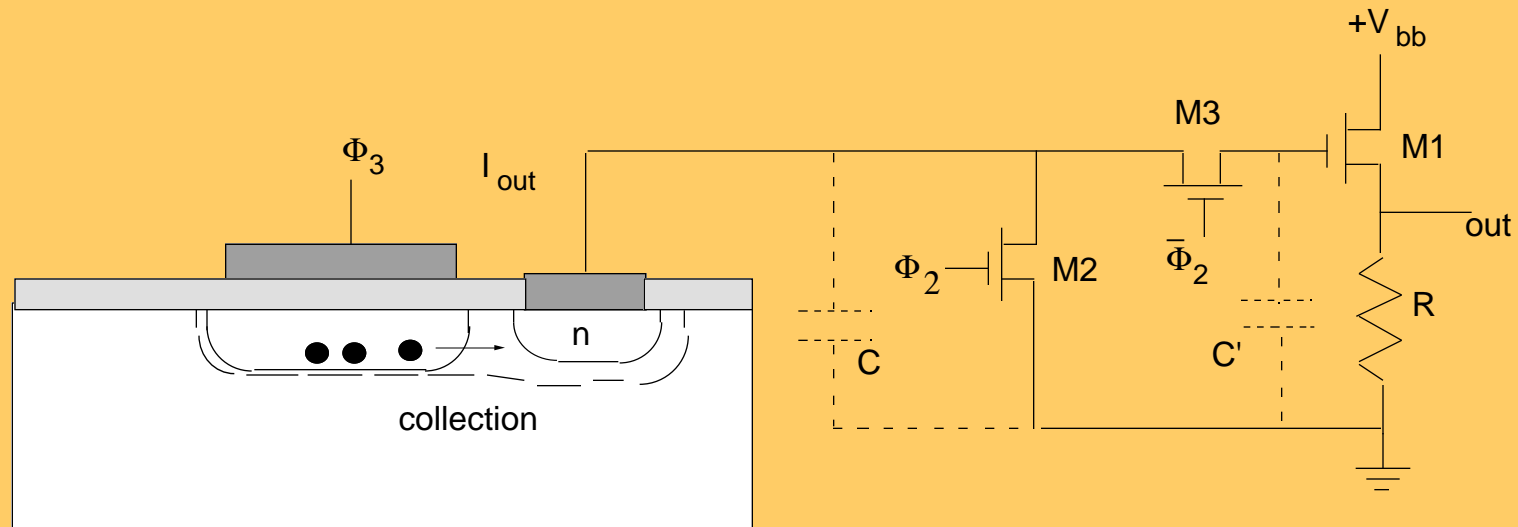
Image organization: CID (charge-injection CCD)



Infrared MSA

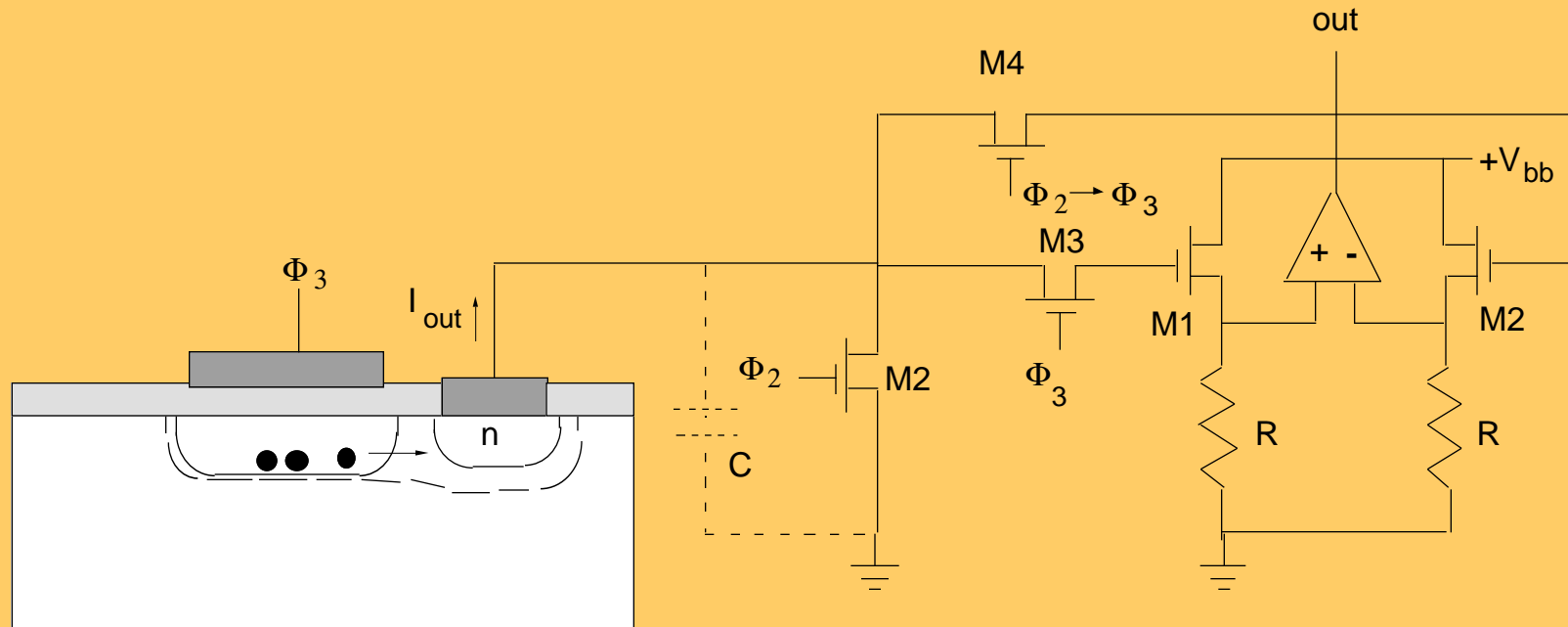


Output stage



$$\begin{aligned} \text{noise: } v_n^2 &= 2e[FI_{ph} + 2nI_d]B R^2 + (8/3) kT B/g_m + kT/C + 4kTBR \\ &\approx 2e[FI_{ph} + 2nI_d]B R^2 + (8/3) kT B/g_m + kT/C \quad (\text{for } g_m R \gg 1) \end{aligned}$$

Correlated double-sampling output stage



noise: $v_n^2 = 2e[FI_{ph} + 2nI_d]B R^2 + (8/3) kT B/g_m$
 $i_n^2 = 2e[FI_{ph} + 2nI_d]B + (8/3) kT B/g_m R^2$